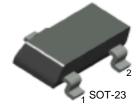


KST4124

General Purpose Transistor



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current	200	mA
Pc	Collector Dissipation	350	mW
T _{STG}	Storage Temperature	150	°C

Refer to KST3904 for graphs

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =10μA, I _E =0	30		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C =1.0mA, I _B =0	25		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	5		V
I _{CBO}	Collector Cut-off Current	V _{CB} =20V, I _E =0		50	nA
I _{EBO}	Emitter Cut-off Current	V_{EB} =3V, I_{C} =0		50	nA
h _{FE}	* DC Current Gain	V_{CE} =1V, I_{C} =2mA V_{CE} =1V, I_{C} =50mA	120 60	360	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C =50mA, I _B =5.0mA		0.3	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C =50mA, I _B =5.0mA		0.95	V
f _T	Current Gain Bandwidth Product	I _C =10mA, V _{CE} =20V f=100MHz	300		MHz
C _{ob}	Output Capacitance	V _{CB} =5V, I _E =0, f=1.0MHz		4	pF
NF	Noise Figure	I_C =100μA, V_{CE} =5V R_S =1KΩ f =10Hz to 15.7KHz		5	dB

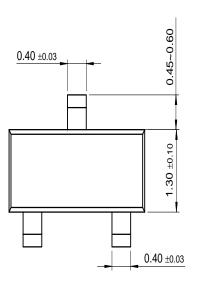
^{*} Pulse Test: PW≤300μs, Duty Cycle≤2%

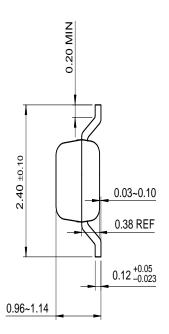


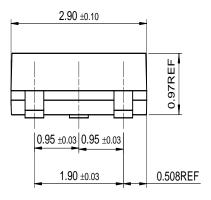
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Package Demensions

SOT-23







Dimensions in Millimeters

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